

IMPLEMENTING TRAPPED-ION ARCHITECTURES FOR ANALYSIS OF DATA

Experimental:

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John Aidun

9 January 2014

NIST Boulder

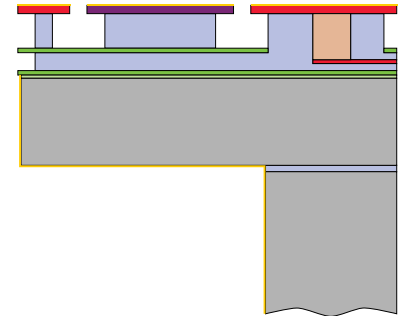
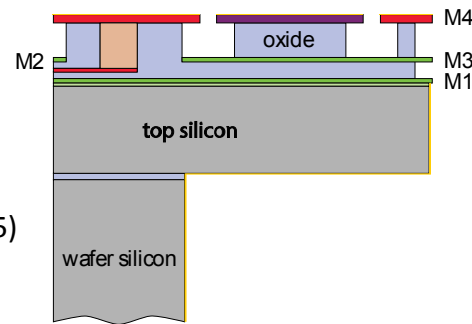
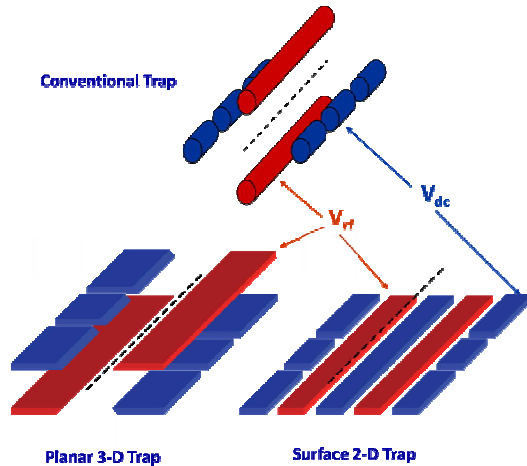
SAND document number: *tbd*

Milestones & Deliverables

Date	Milestone/deliverable
8/13	Redesign three-ion Triangle trap (not stated in SOW)
9/13	Fabricate the three-ion triangle trap mounted on the high-optical-access platform.
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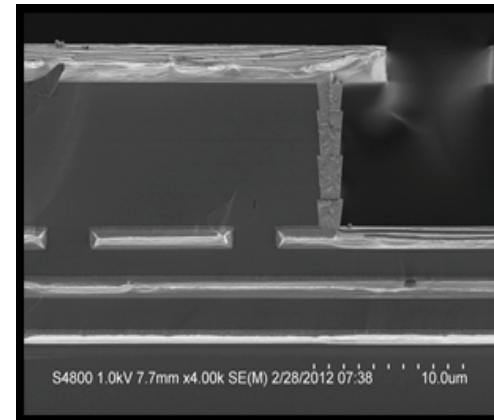
Surface Electrode Ion Trap Fabrication

4-metal-layer process modified from Sandia 0.35 μm Al/SiO₂ CMOS Process



J. Chiaverini, *et al.*, *Quant. Inf. Comp.* 5, 419 (2005)

- 1.2/2.5 μm Al 4LM technology
- Trap flow: ~ 300 ops, 11 mask levels used 17x
- Interposer flow: ~ 320 ops, 15 mask levels used 21x
- 10 μm oxide separating RF(M4), ground (M3)
- Precision Chip thru-holes
- Release singulation
- Precisely recessed oxide
- Routing on M2
- Gold coating from front and back side



Possible geometries

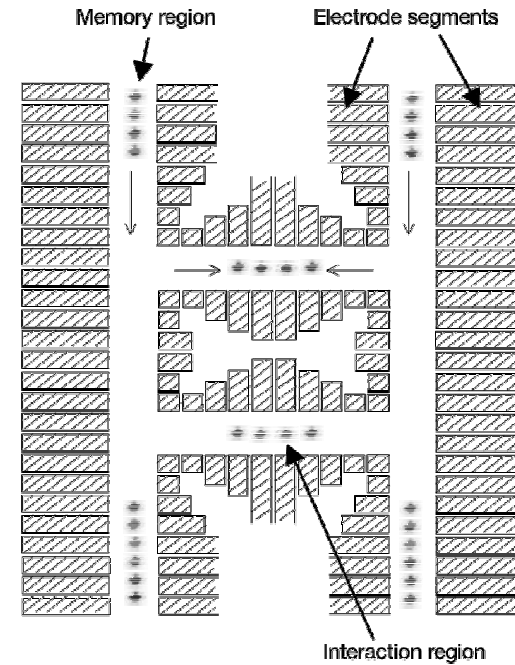
multi-layer technology advantages

Reminder

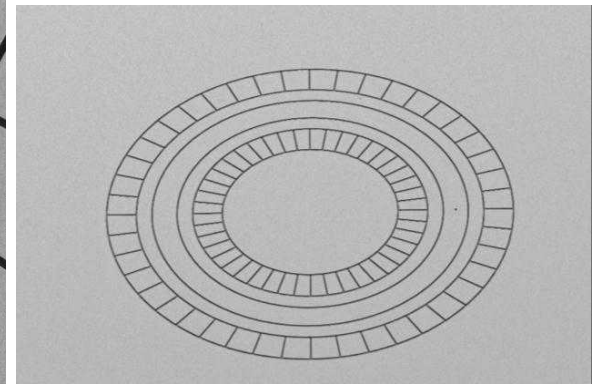
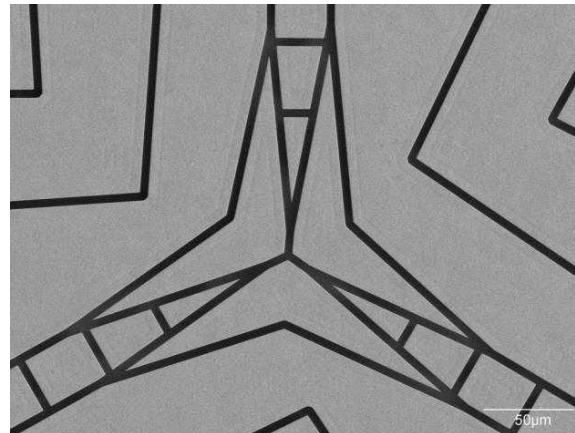
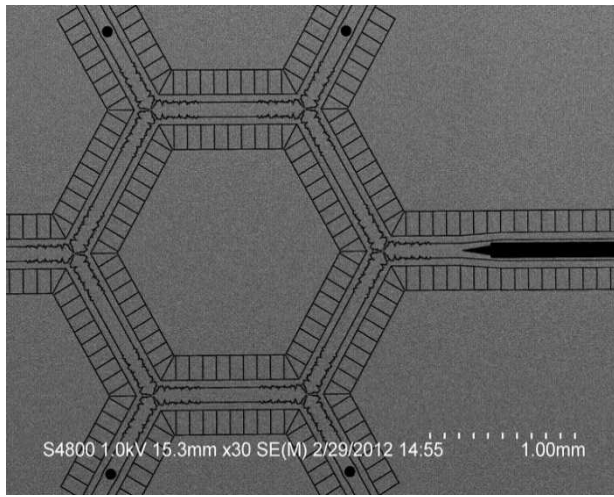
4-level-metal devices allow for:

- No exposed routing
- Islanded electrodes
- New topologies
- **5th layer for dense routing**

Arbitrary trap geometries
can be realized



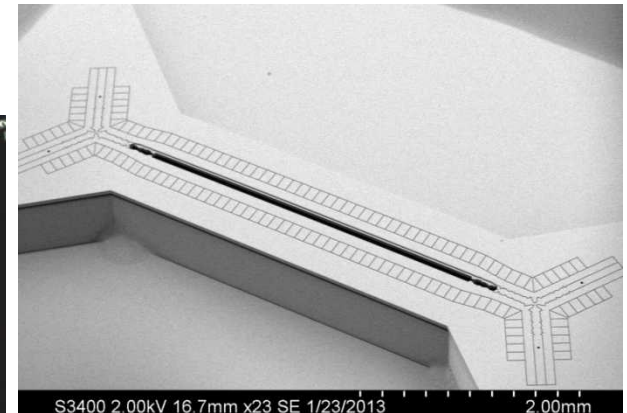
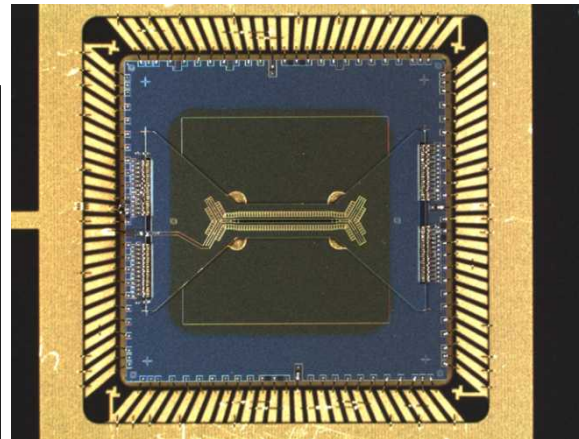
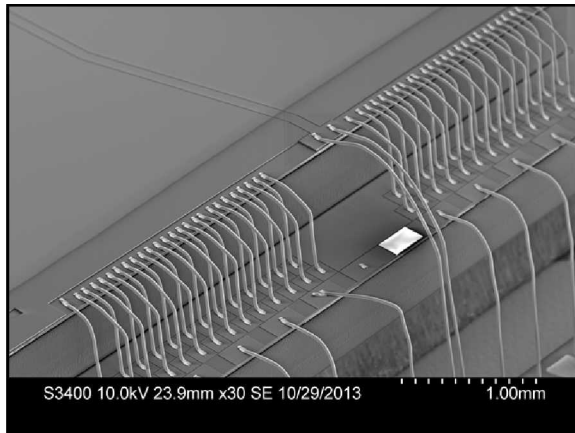
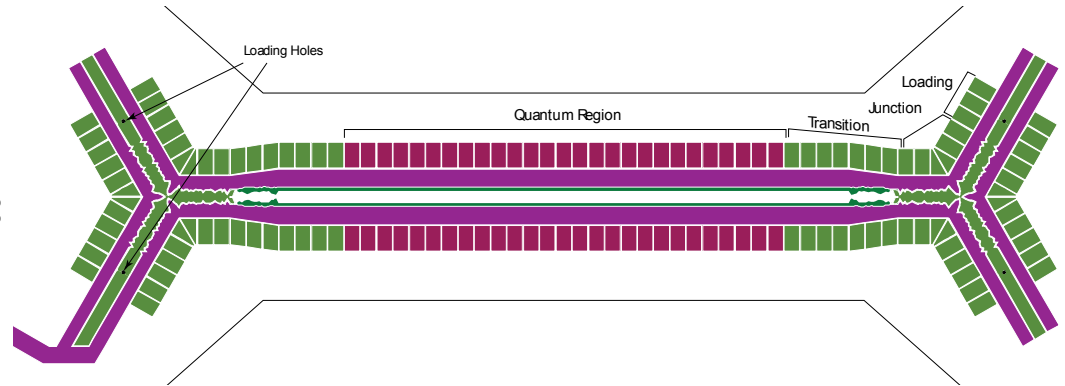
D. Kielpinski, *et al.* Nature 417, 209 (2002).



HOA trap platform: high optical access trap

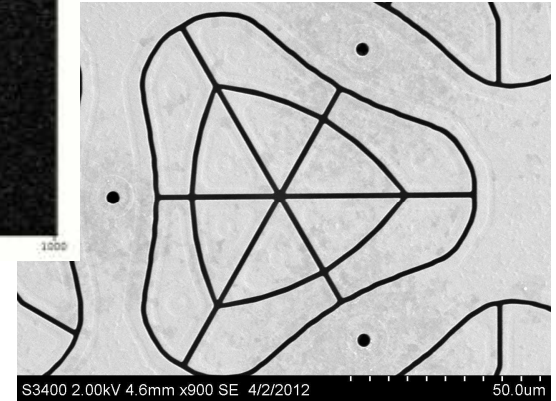
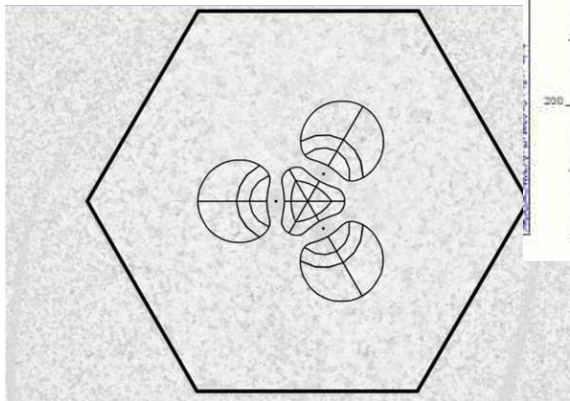
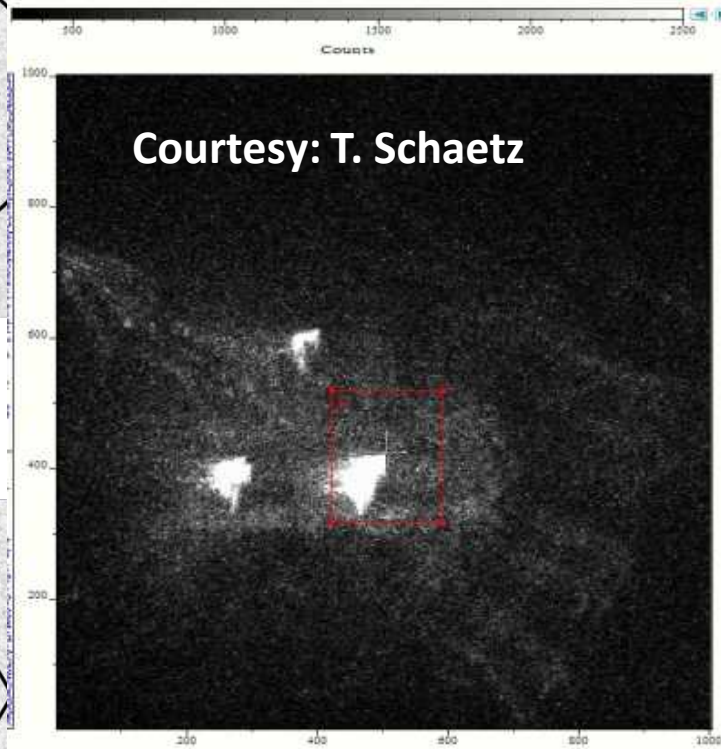
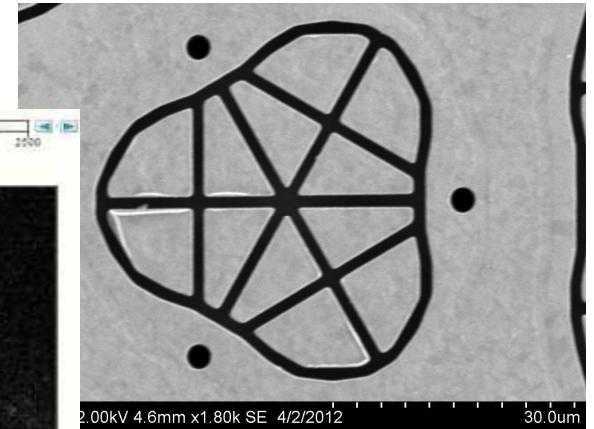
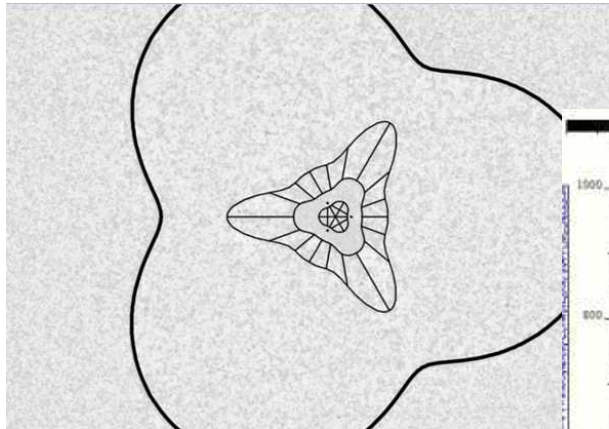
Optimized surface electrode ion trap platform

- Release singulation allows for arbitrary chip shapes
- Greatly improved optical access:
 - Larger trap depth
 - Higher trap frequencies
 - Less optical scatter



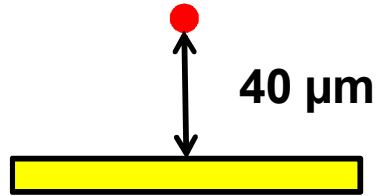
Original Triangle Trap (Rev 0) – 80 μm , 40 μm triangles

40 μm triangles

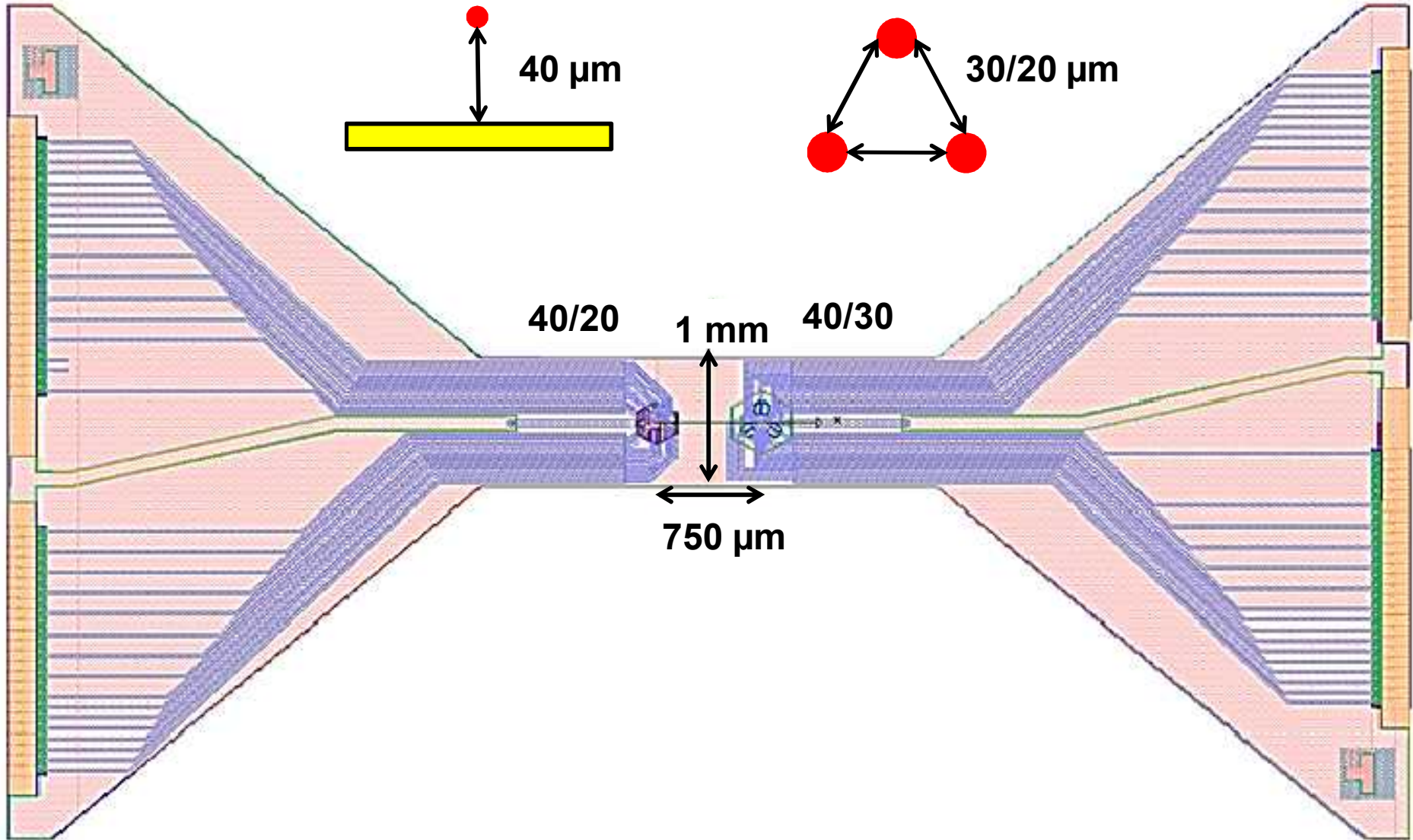
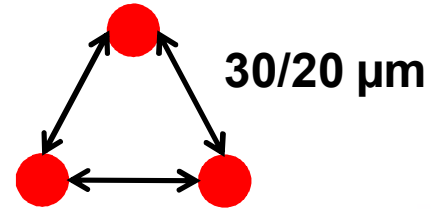


New Triangle Trap

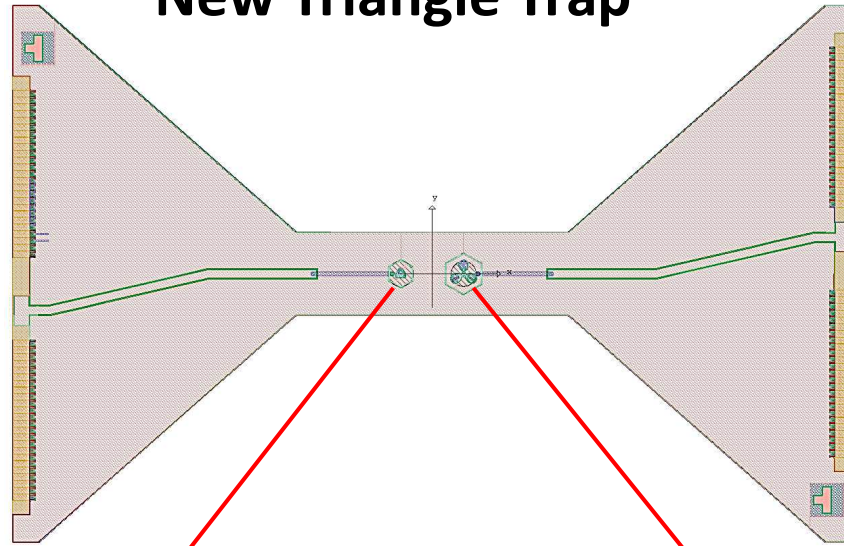
ion height fixed



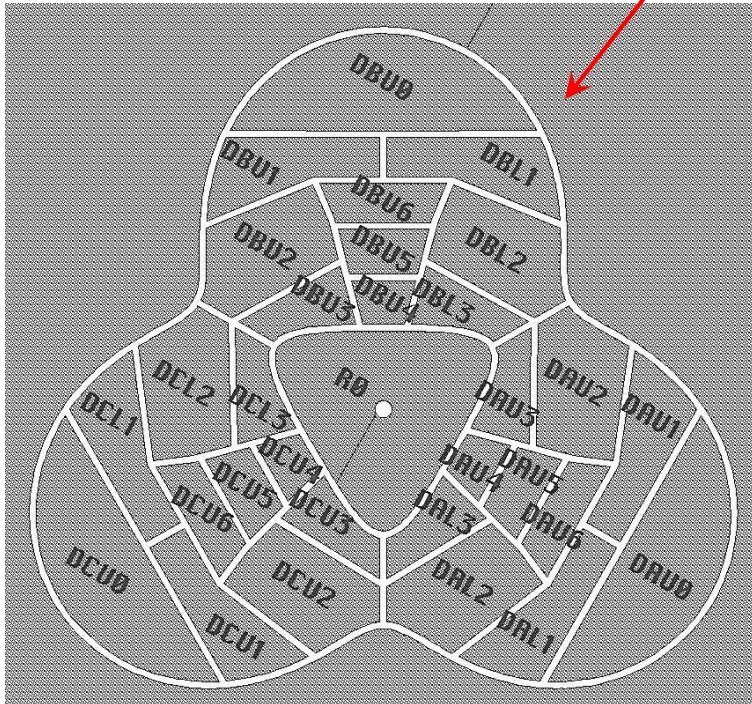
ion-ion distance reduced



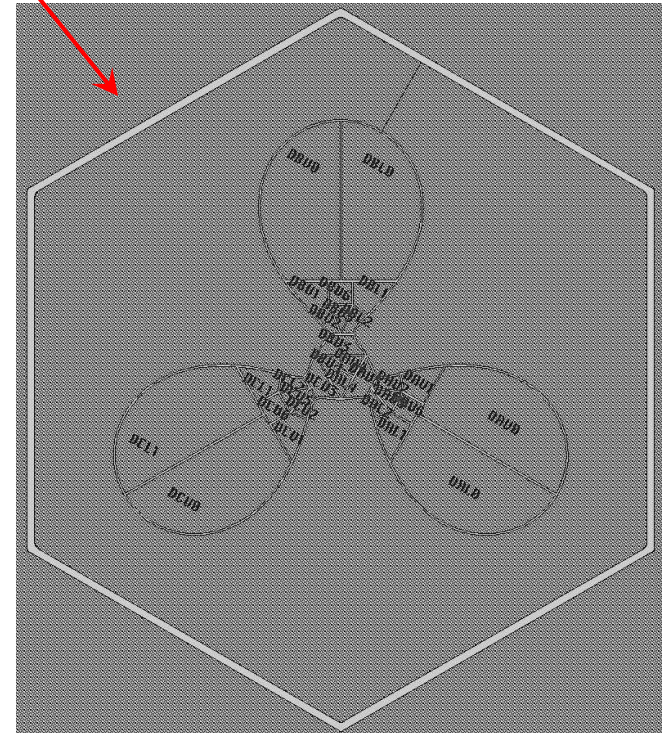
New Triangle Trap



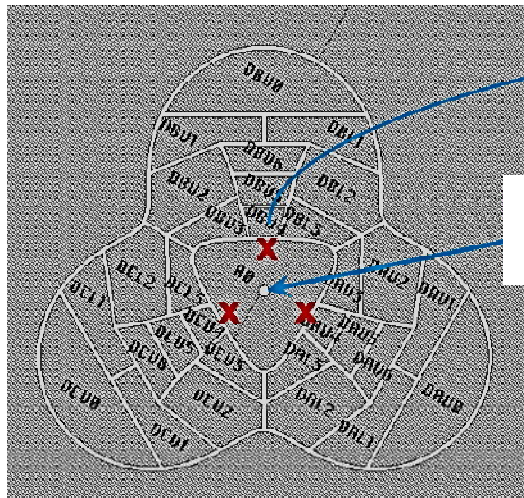
40/20



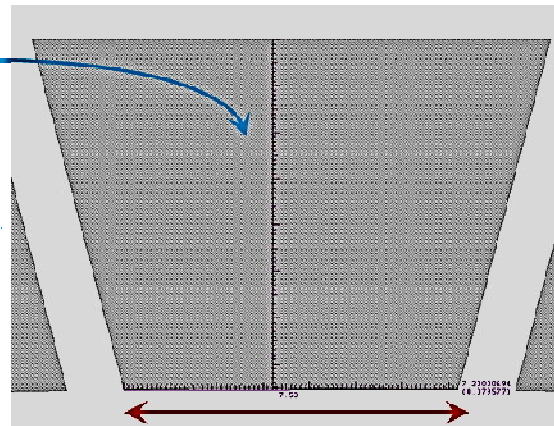
40/30



New Triangle Trap – Smallest Surface Trap

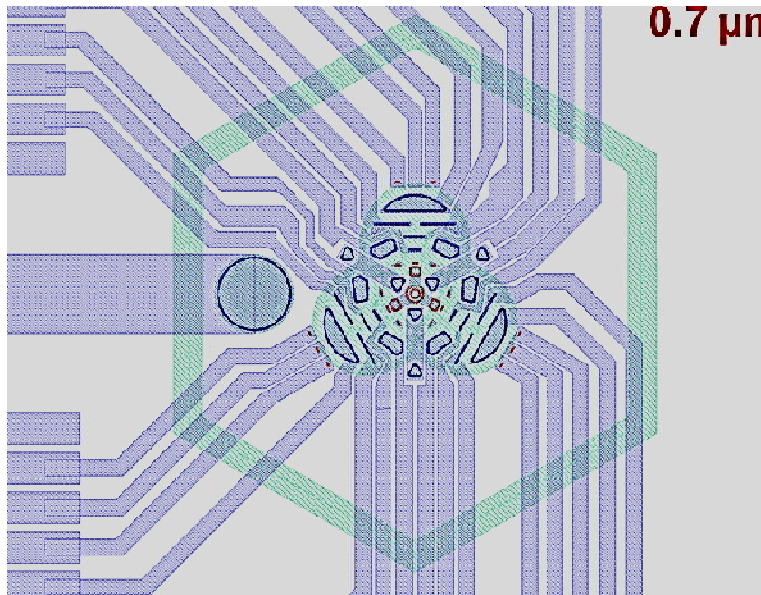


Ion spacing: 20 μm
 Ion height: 40 μm

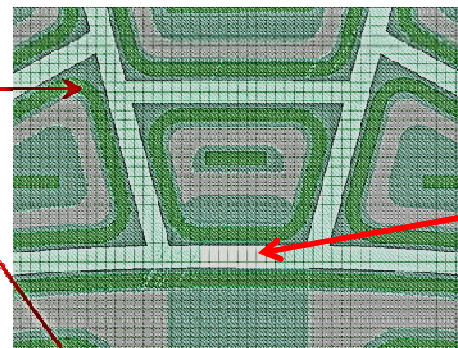


7.53 μm

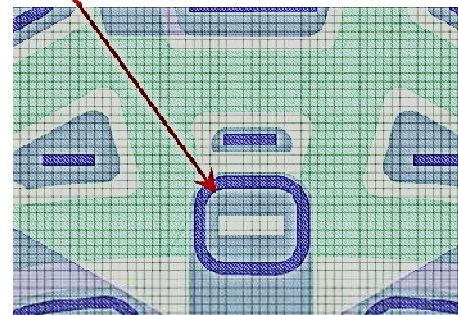
7.2 μm



0.7 μm vias

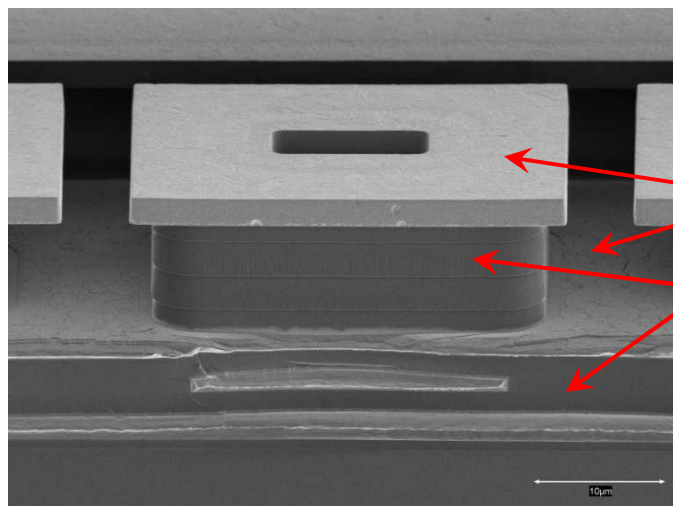
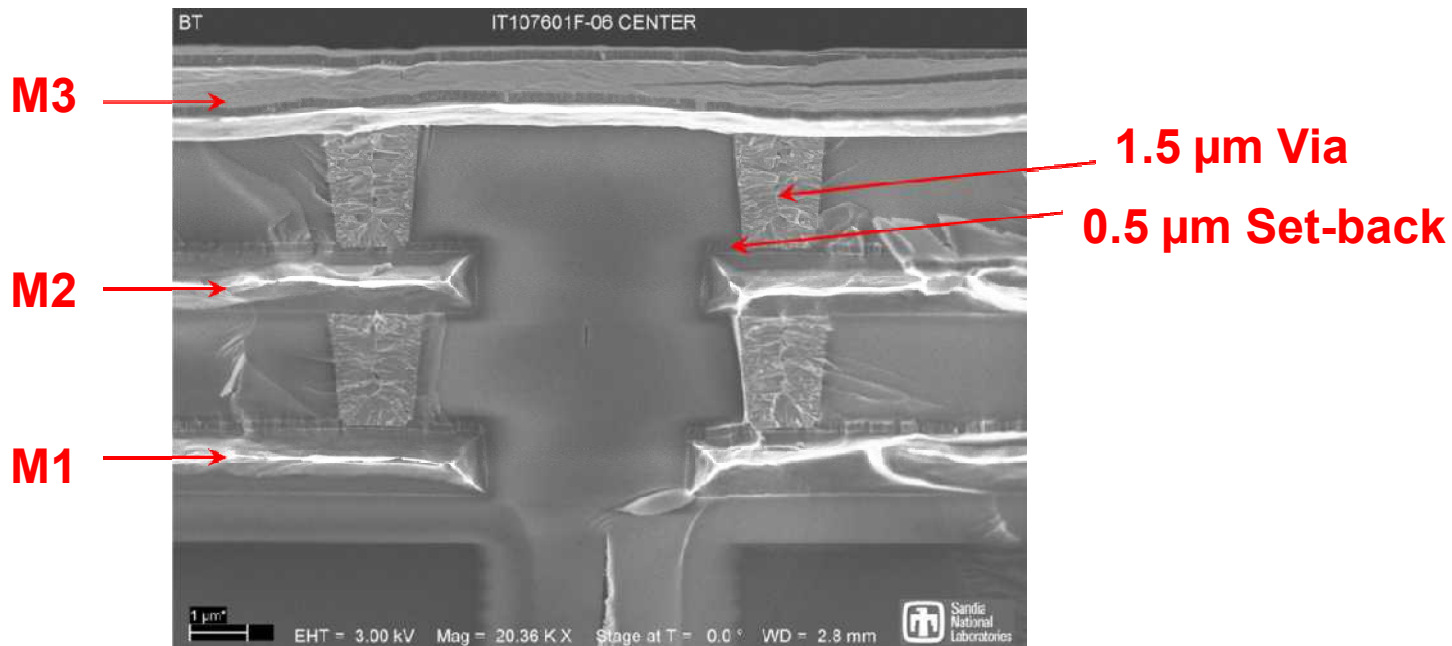


1.2x2.5 μm^2
 Loading slot



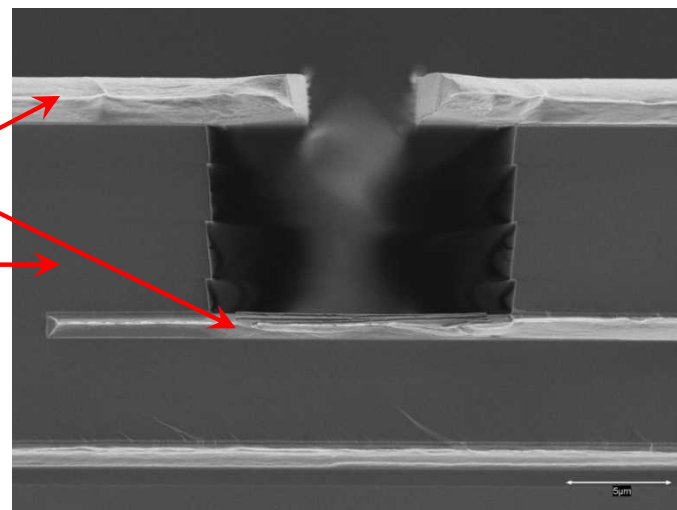
Loading thru gap
 in M4 electrodes;
 loading hole in M3

The importance of vias



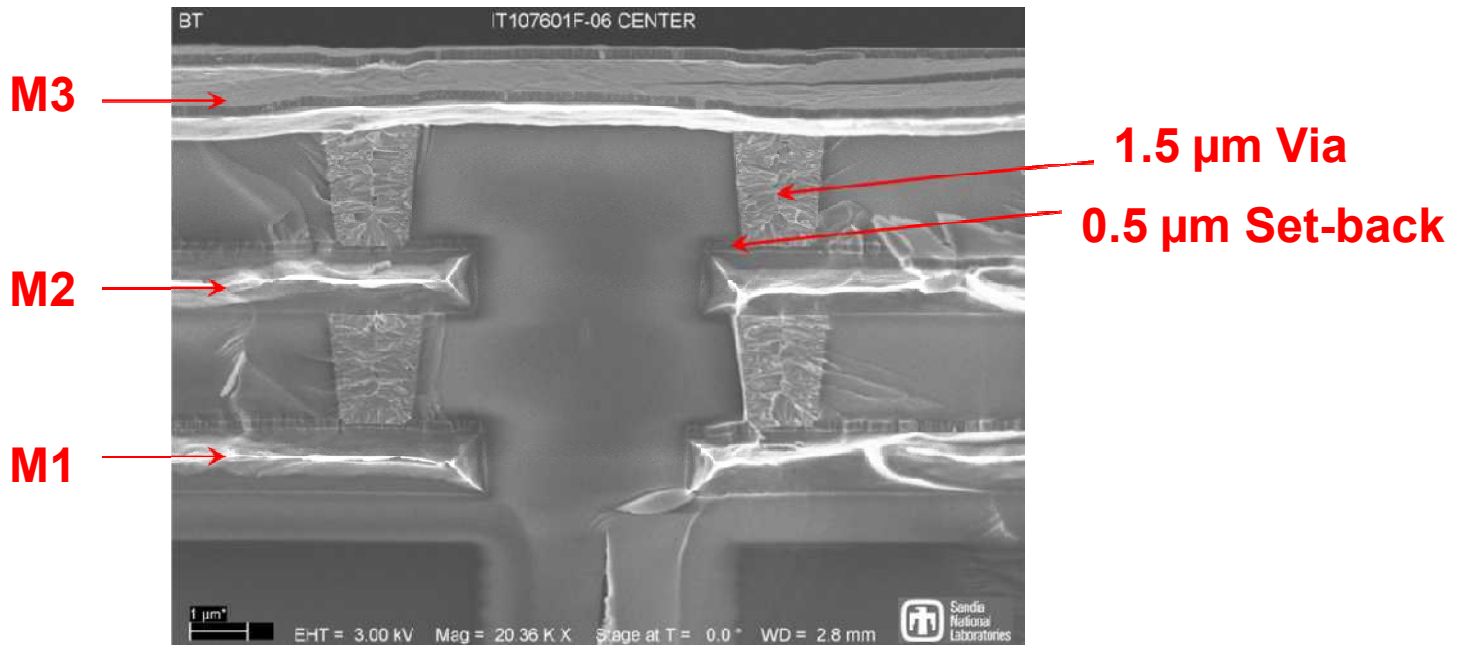
Metal

Dielectric



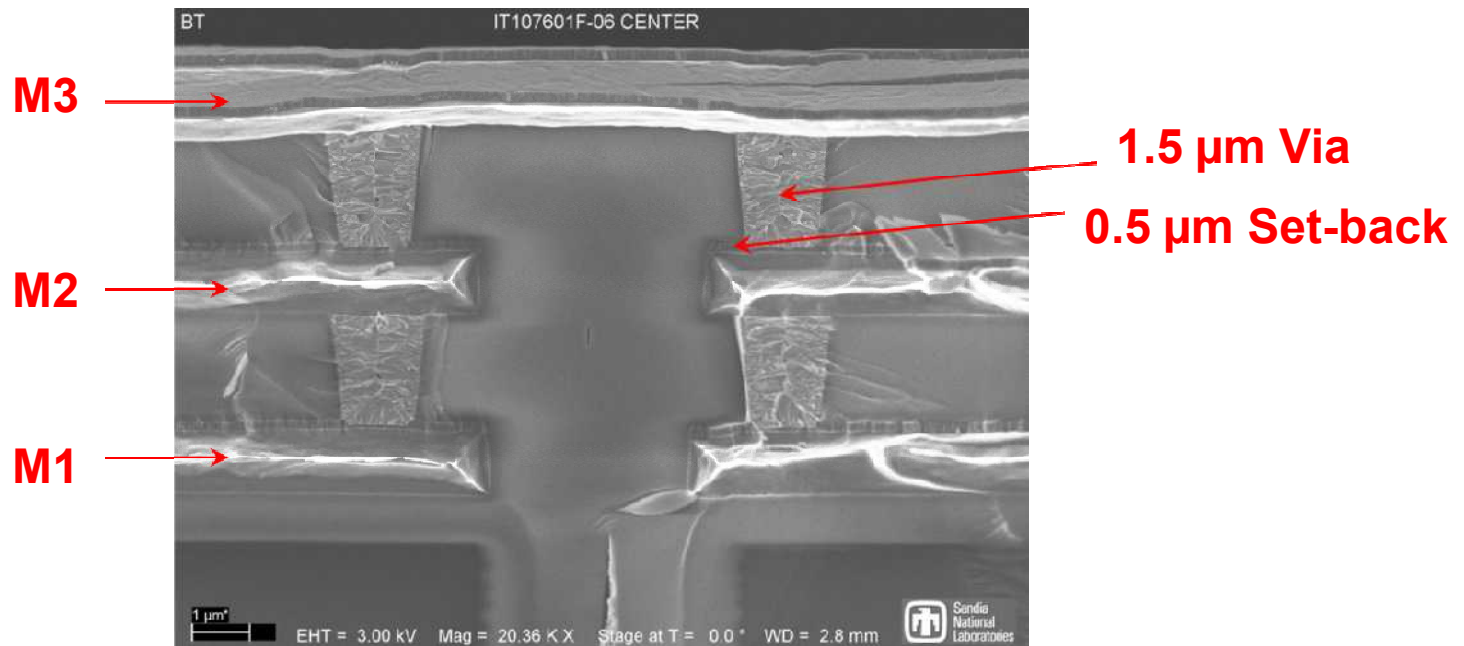
Ion Trap Minimum Electric Rules – 1.5 μm Vias

Minimum Electric Rule (μm)	RS (Release Seam)	MO (Marks Only)	M1 (Metal 1)	V1 (Via 1)	M2 (Metal 2)	V2 (Via 2)	M3 (Metal 3)
Min Width	4	N/A	5	1.5	5	1.5	5
Min Space (preferred)	5*	N/A	3	3	3	3	3
Min Space (Acceptable)	3*	N/A	2.5	2	2.5	2	2.5



Ion Trap Minimum Electric Rules – 1.5 μm Vias

Minimum Electric Rule (μm)	V3 (Via 3)	V3-2 (Via 3-2 nd level)	V3-3 (Via 3-3 rd level)	V3-4 (Via 3-4 th level)	M4 (Metal 4)	HS (Head start)	BS (Backside)
Min Width	1.5	1.5	1.5	1.5	5	3	50
Min Space (preferred)	3	3	3	3	5	N/A	50
Min Space (Acceptable)	2	2	2	2	2.5	N/A	50



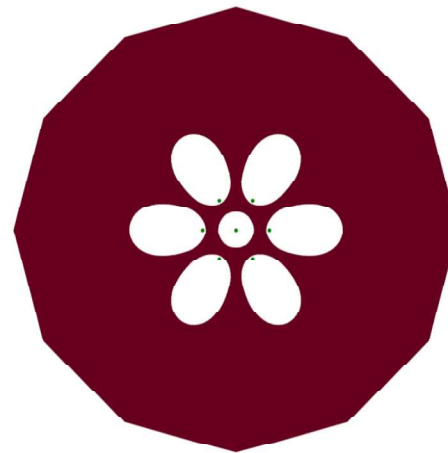
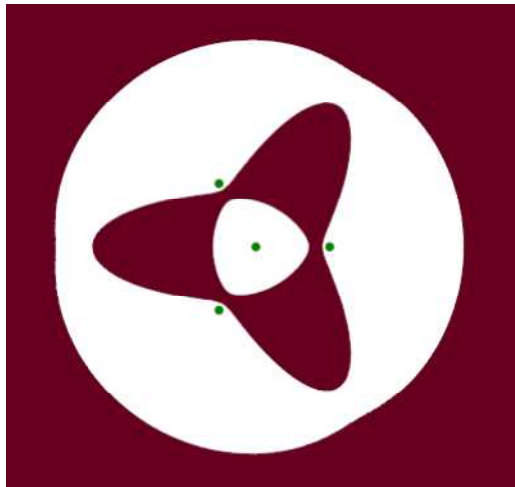
Trap Status

New Triangle Trap

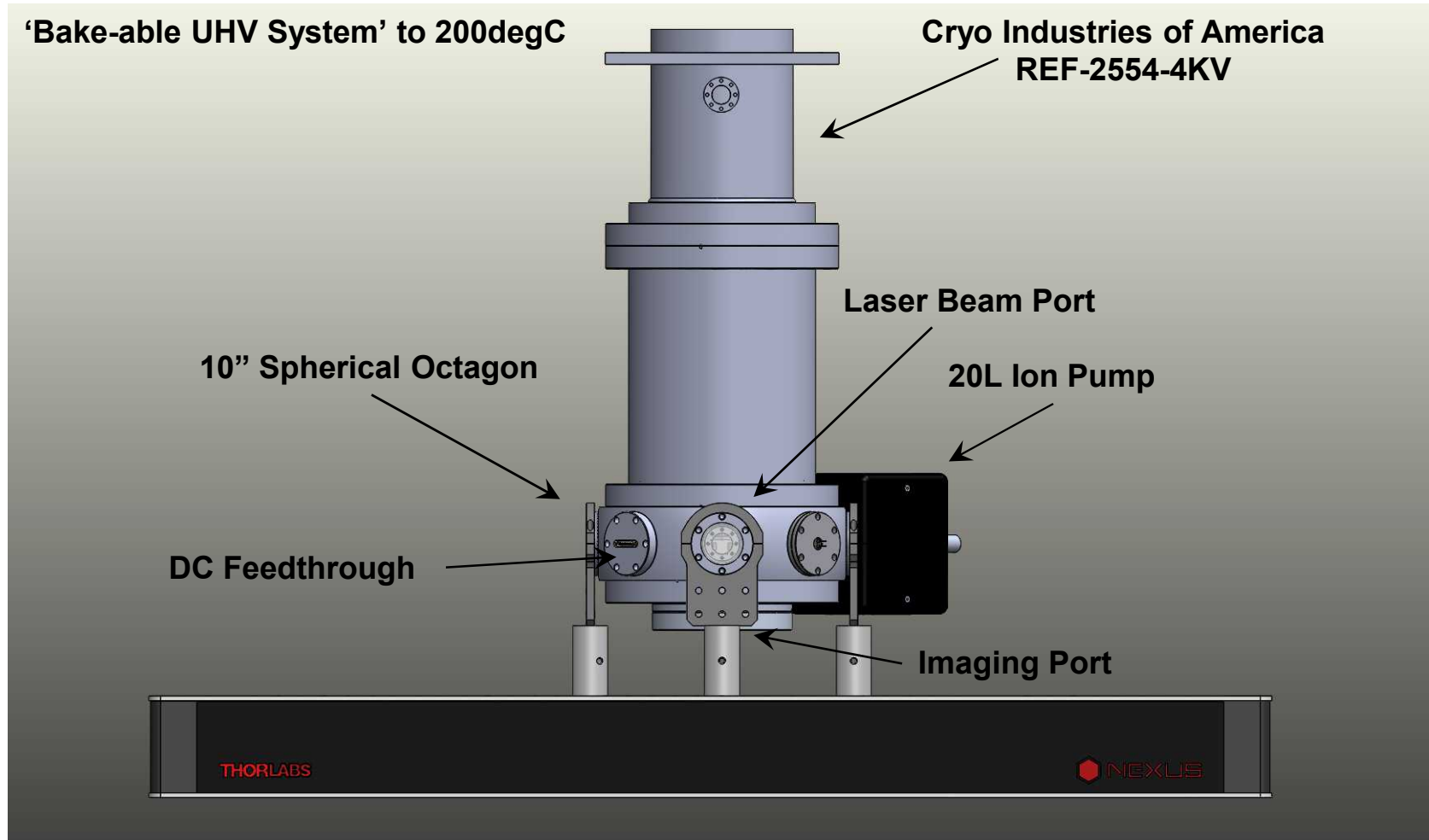
- Two new triangle designs (20 μm /30 μm) simulated by NIST (Robert)
- 1st two photomask levels ordered, lot started November 2013
- Short loop diagnostics mask completed
- Initial short loop experiments for making very small electrodes completed
- Photomask routing/layout for remaining 9 levels in progress, completion projected 1/2014
- Device fabrication/packaging of triangle traps completion projected 4/2014

Hex+Center Trap

- Initial design of 3+1 and 6+1 4LM surface electrode trap received from NIST
- Photomask routing/layout completion projected 2/2014, pending final design



Cryogenic Ion Trap System



Cryogenic Industries of America

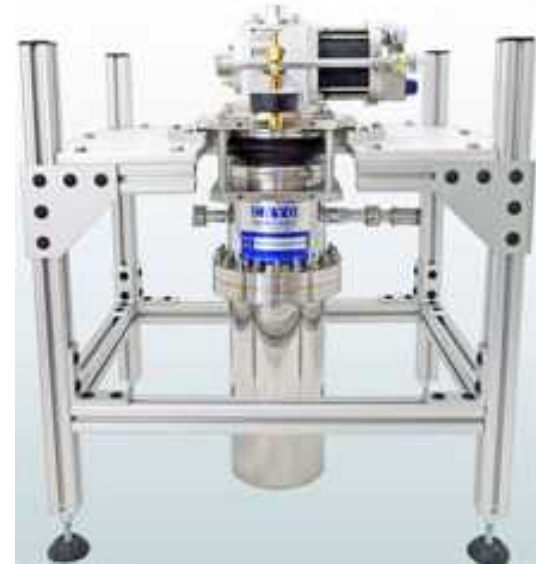
http://www.cryoindustries.com/pdf/CF_Low_Vibration.pdf



Gifford McMahon Cryo-Cooler
~1Hz Cycle

Isolation Bellows

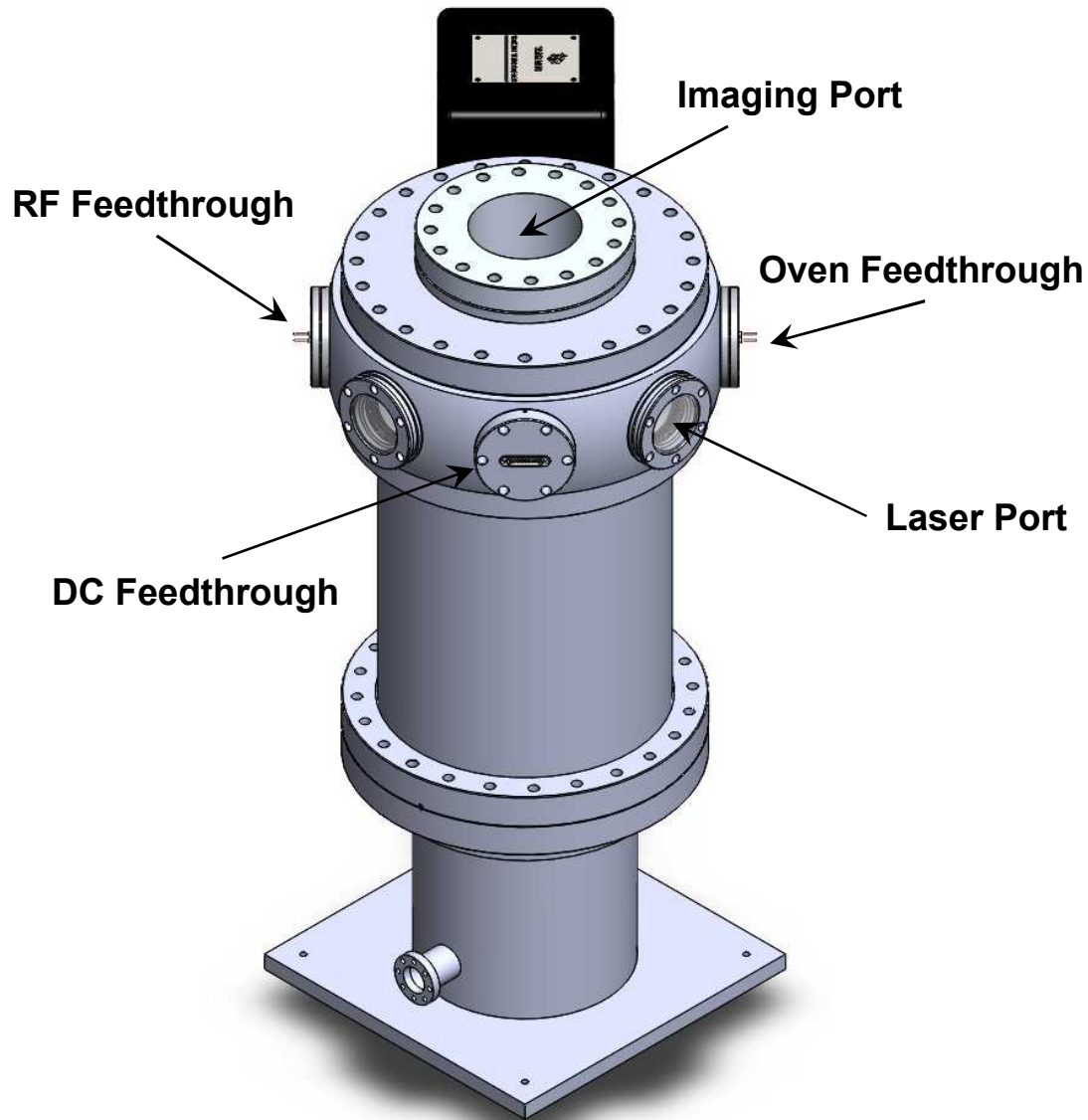
UHV Chamber



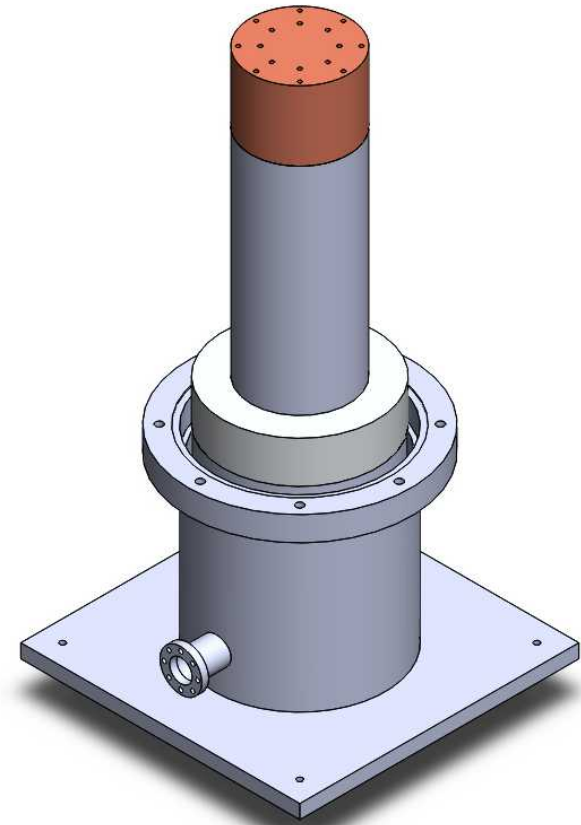
Cryo Industries of America

- 1.0 Watt @ 4K – Cooling Power
- 34.0 Watt @ 40K – Cooling Power
- Gifford McMahon (GM) – Closed Cycle
- Bellows Vibration Isolated Coldfinger
 - Exchange Gas Cooled

Cryogenic Ion Trap System

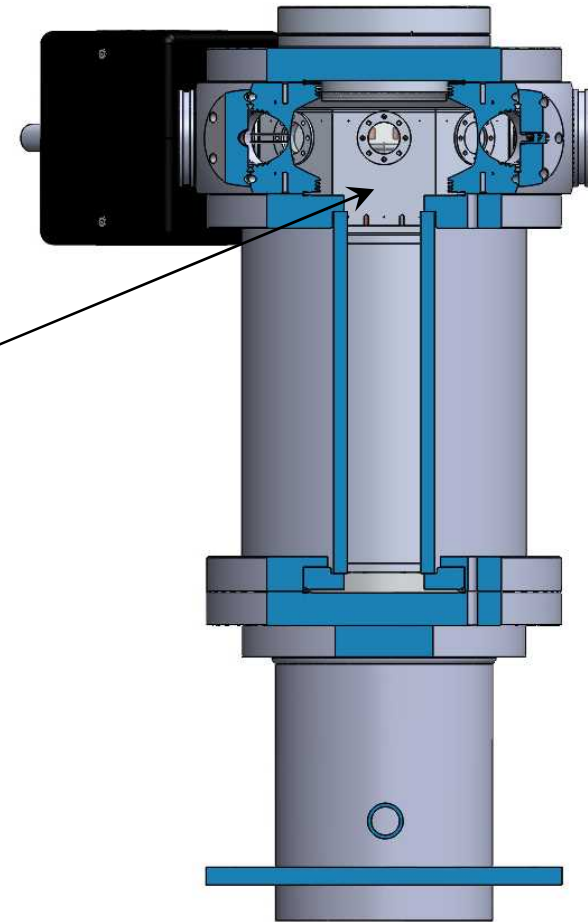
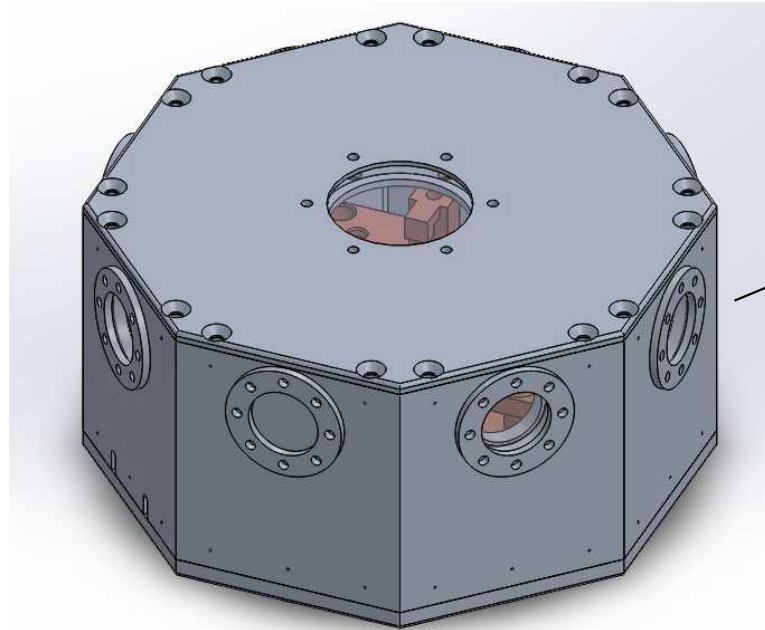


Vibration Isolated Coldfinger



Cryo-system: What's Inside?

Experimental Carriage



**Modular Experimental Carriage –
Allows system to be assembled
independent of cryostat**

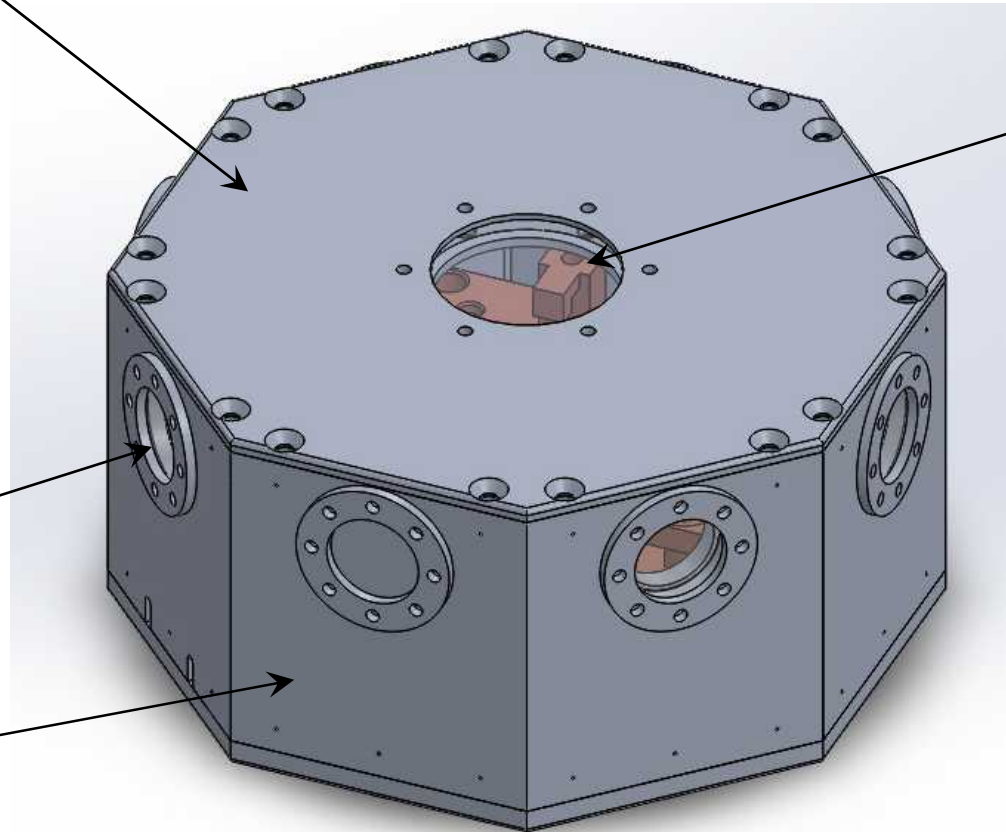
Cryo-system: What's Inside?

Radiation Shield – tied to first stage cooling

Imaging Port

Laser Port

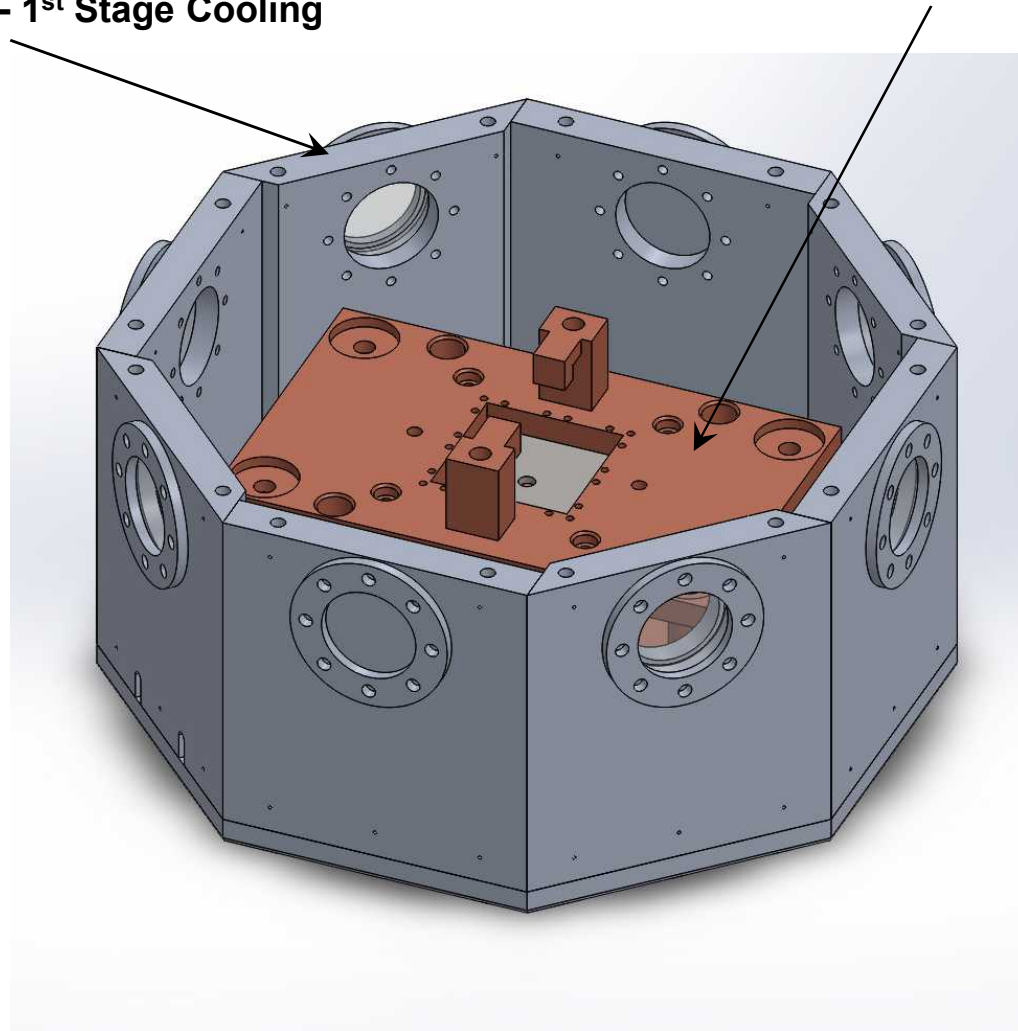
Swappable Walls



Cryo-system: What's Inside?

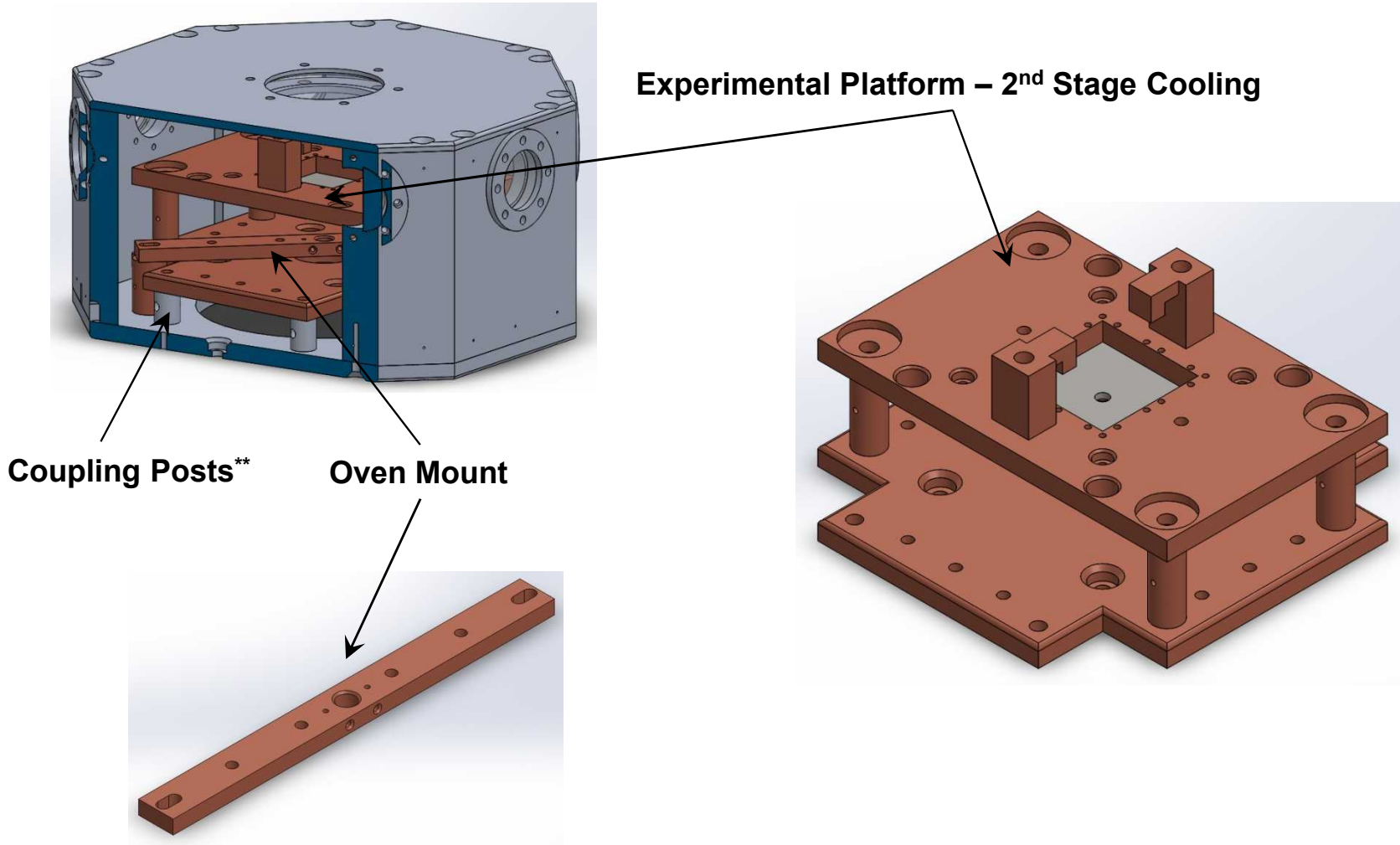
Radiation Shield – 1st Stage Cooling

Experimental Platform – 2nd Stage Cooling



****Radiation Shield and Experimental Platform are independent during operation**

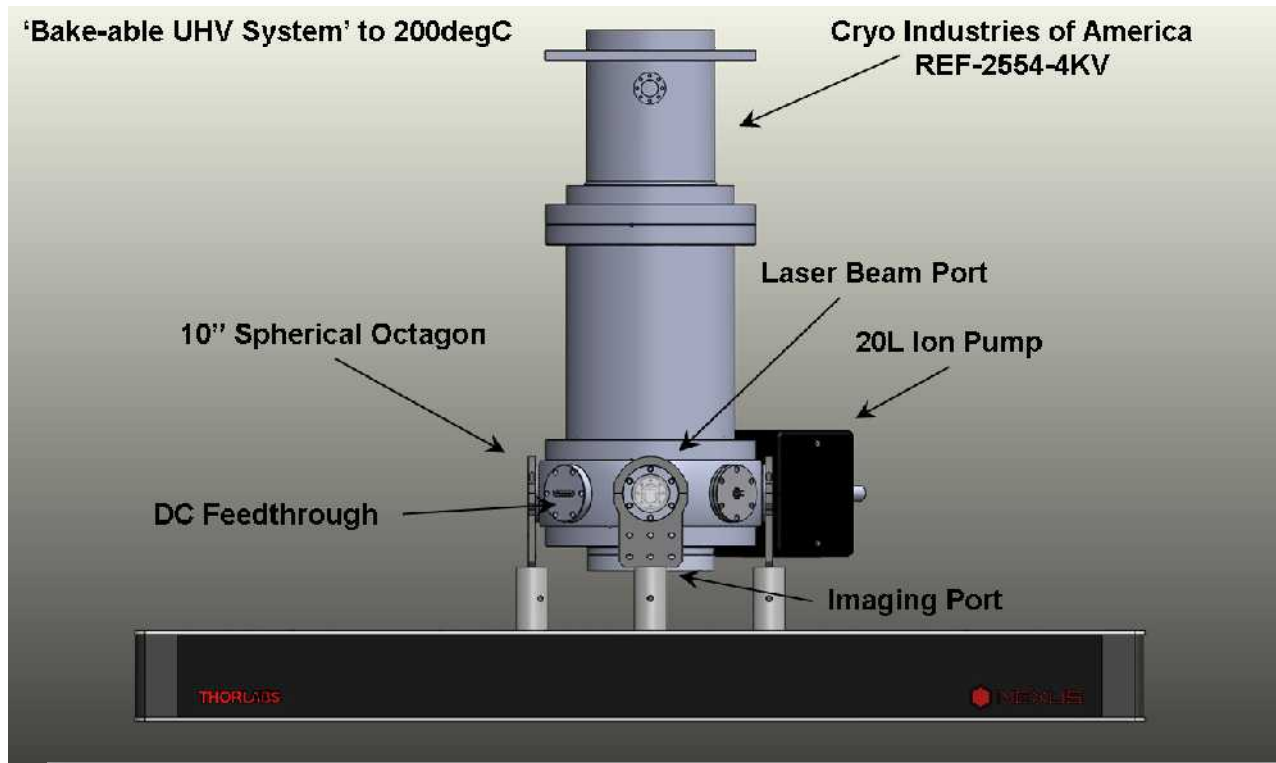
Cryo-system: What's Inside?



****Removed After Assembly of System**

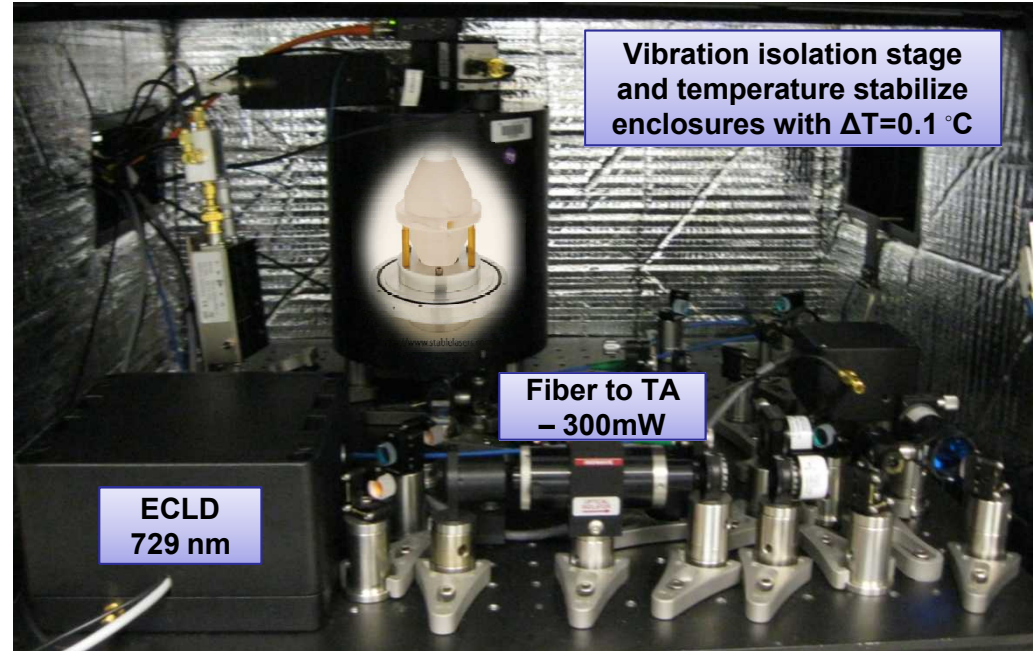
Cryo Status

- Cryostat ordered from Cryo-Industries of America December 2013 (2-3 month lead time)
- Laboratory modification due to start January 2014, completion projected February 2014
- Assembly of cryostat to start upon arrival and be completed in 3-4 months , projected June 2014
- Successfully trap ions in cryostat by August 2014



Progress towards Qubit operations

ULE Optical Cavity Fabry-Perot cavity (ATFilms 6030)

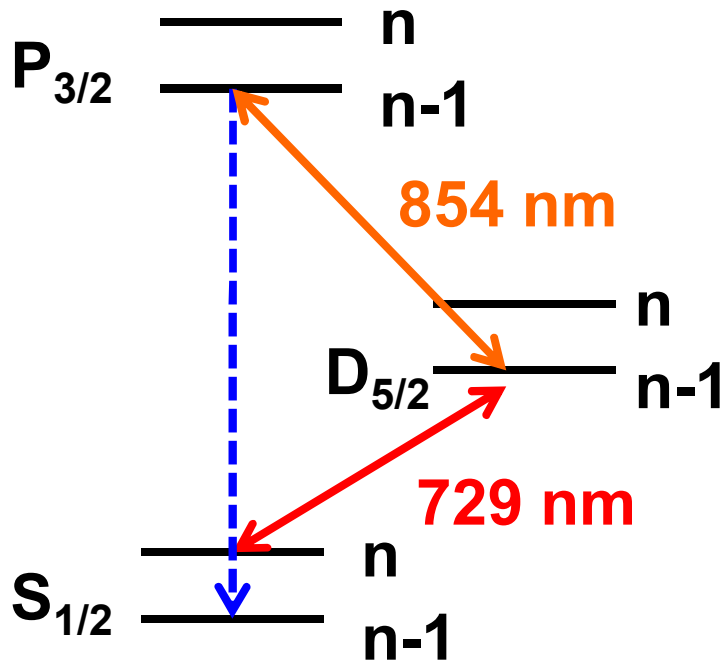


Vibration isolation stage and temperature stabilize enclosures with $\Delta T = 0.1^\circ\text{C}$

Fiber to TA
- 300mW

ECLD
729 nm

Calcium Optical Qubit



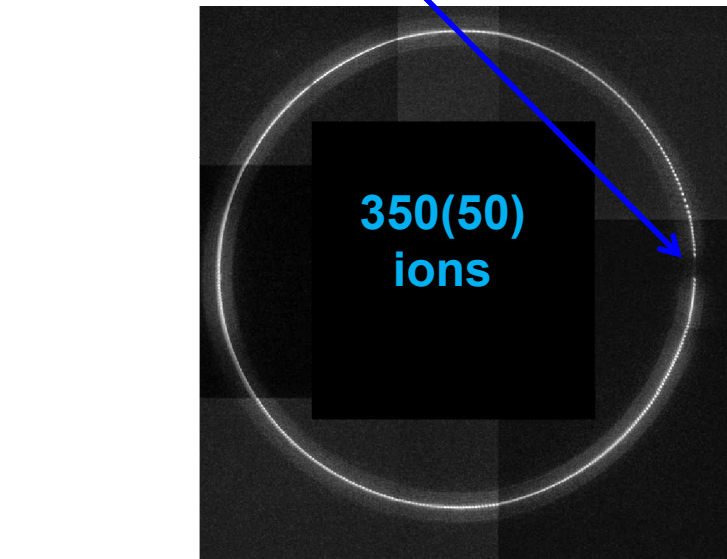
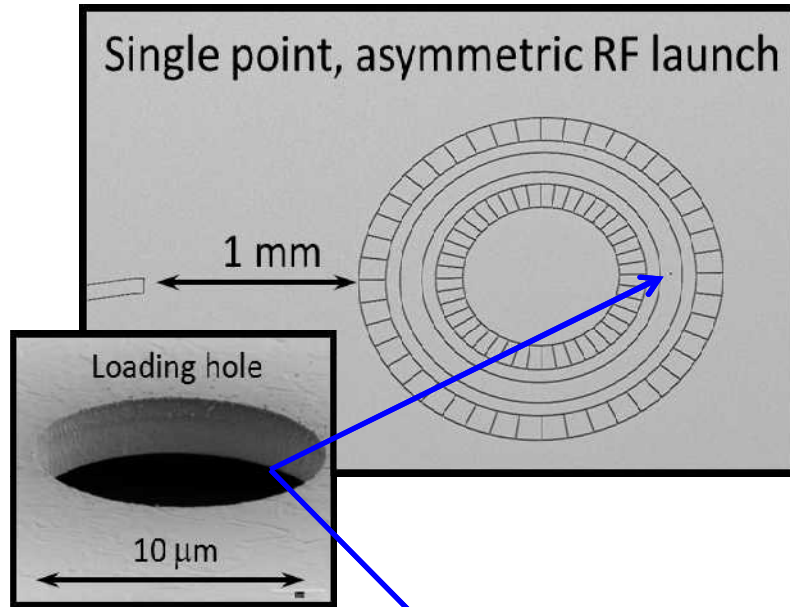
$$F = 200000$$

$$\nu_F = 1.93 \text{ GHz}$$

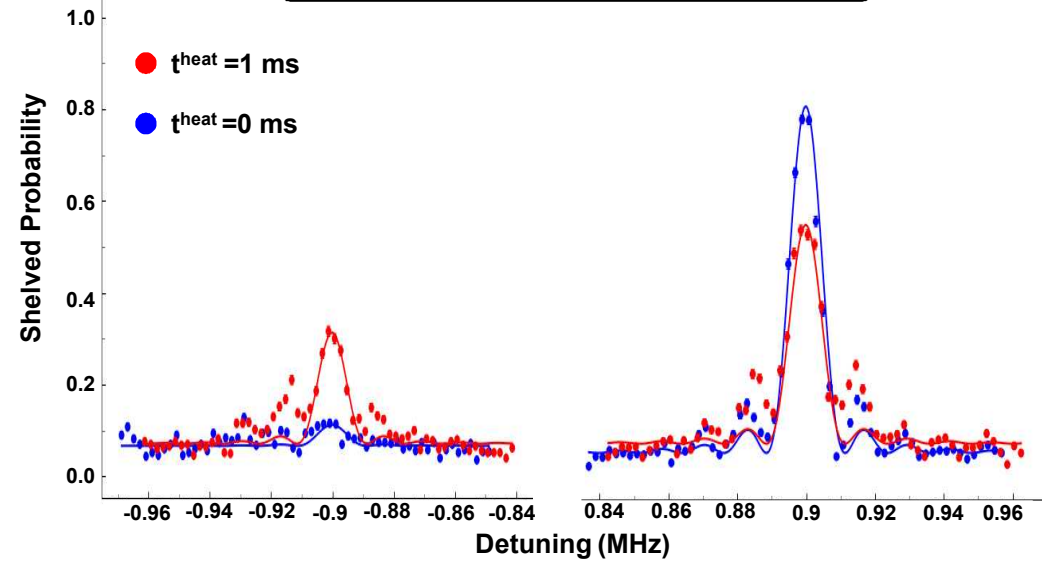
$$\delta_\nu = \frac{\nu_F}{F} = 9.65 \text{ kHz}$$

$$T_c = 24.2^\circ\text{C}$$

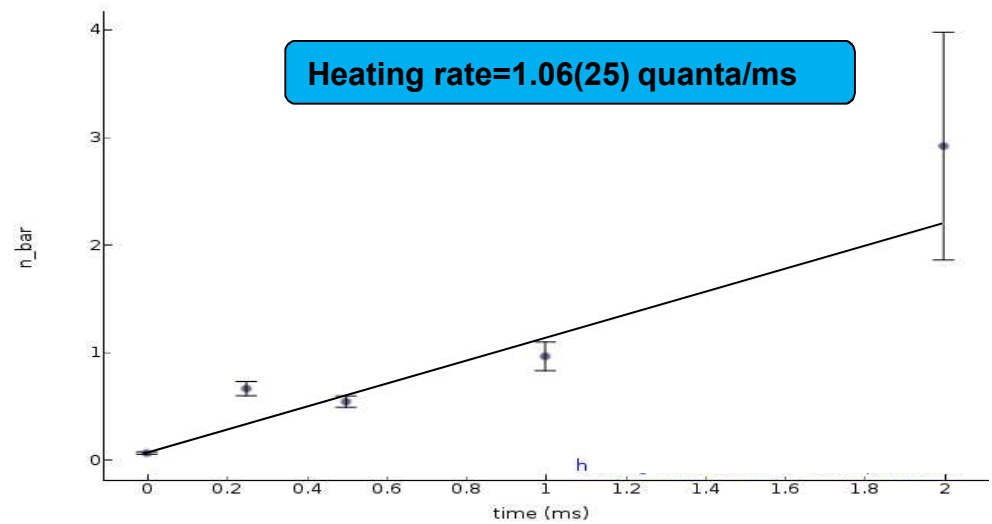
Progress towards Qubit operations



Heating Rate Measurements



Heating rate = 1.06(25) quanta/ms



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